AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) An electromagnetic wave detecting device, comprising:

a semiconductor film which generates a charge upon induction by an electromagnetic wave; and

an active matrix array for reading out the charge which is generated in the semiconductor film,

wherein:

the active matrix array is formed by having a resin substrate as its base and detects the electromagnetic wave by a direct converting system[[.]], and the resin substrate has a curved shape.

2. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: the semiconductor film has Se as its major component.

3. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: the semiconductor film is formed as a continuous film to cover a surface of the active matrix array.

[redacted]

4. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: the semiconductor film and the active matrix array are respectively formed on different substrates, thereafter being joined together.

5. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: the semiconductor film includes a photoconductive organic material as its major component.

6. (Canceled)

7. (Currently amended) The electromagnetic wave detecting device set forth in claim [[6]] 1, further comprising: a supporting material having a curved shape formed on one side of the resin substrate which is opposite to a side having the semiconductor film formed thereon.

8. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: at least one side of the resin substrate is coated with a gas barrier layer.

9. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: one side of the resin substrate having the semiconductor film formed thereon is covered with a resin layer.

[redacted]

10. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: a thermal expansion coefficient x(/°C) of the resin substrate is within a range of $1.0 \times 10^{-5} < x < 1.0 \times 10^{-4}$.

11. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: a thermal expansion coefficient y(/°C) of the semiconductor film is within a range of $30 \times 10^{-6} < y < 50 \times 10^{-6}$.

12. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: a thickness z(mm) of the resin substrate is within a range of $0.1 < z < 0.7$.

13. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: the resin substrate is flexible.

14. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: the active matrix array includes a TFT element, charge storage capacitance, a charge collector electrode, a scanning electrode, and a data electrode.

[redacted]

15. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: the resin substrate has an organic-inorganic hybrid material as its major component.

16. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: the resin substrate includes as its major component a material which is a combination of a plurality of organic compounds.

17. (Original) The electromagnetic wave detecting device set forth in claim 1, wherein: CdTe is used as a material of the semiconductor film.

18. (Original) The electromagnetic wave detecting device set forth in claim 1, further comprising: a supporting substrate which includes a bias electrode and the semiconductor film.

19. (Original) The electromagnetic wave detecting device set forth in claim 18, which has a structure in which an active matrix substrate and the supporting substrate are connected via conductive connection materials.

20. (Original) A manufacturing method of an electromagnetic wave detecting device, comprising the steps of:

[redacted]

forming an active matrix array on one side of a resin substrate;

setting the resin substrate having the active matrix array formed thereon to a supporting material while deforming the resin substrate to a curved shape; and

depositing a semiconductor film on a surface of the active matrix array deformed to the curved shape.

[redacted]